

MA3S132E

Silicon epitaxial planar type

For switching circuits

■ Features

- Short reverse recovery time t_{rr}
- Small terminal capacitance, C_t
- Super-small SS-mini type package contained two elements, allowing high-density mounting

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit | |
|--|-----------|-------------|------------------|----|
| Reverse voltage (DC) | V_R | 80 | V | |
| Peak reverse voltage | V_{RM} | 80 | V | |
| Forward current (DC) | Single | I_F | 100 | mA |
| | Double | | 150 | |
| Peak forward current | Single | I_{FM} | 225 | mA |
| | Double | | 340 | |
| Non-repetitive peak forward surge current* | Single | I_{FSM} | 500 | mA |
| | Double | | 750 | |
| Junction temperature | T_j | 150 | $^\circ\text{C}$ | |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ | |

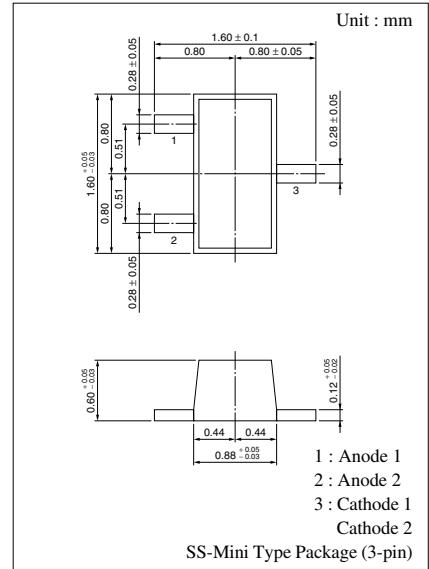
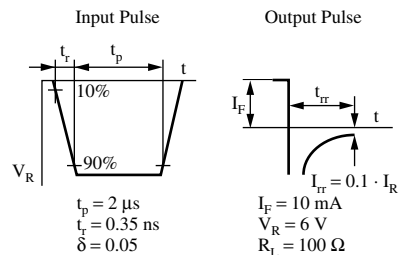
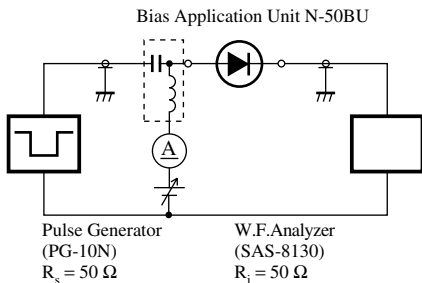
Note) * : $t = 1 \text{ s}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|------------------------|----------|--|-----|-----|-----|------|
| Reverse current (DC) | I_R | $V_R = 75 \text{ V}$ | | | 100 | nA |
| Forward voltage (DC) | V_F | $I_F = 100 \text{ mA}$ | | | 1.2 | V |
| Reverse voltage (DC) | V_R | $I_R = 100 \mu\text{A}$ | 80 | | | V |
| Terminal capacitance | C_t | $V_R = 0 \text{ V}, f = 1 \text{ MHz}$ | | | 2 | pF |
| Reverse recovery time* | t_{rr} | $I_F = 10 \text{ mA}, V_R = 6 \text{ V}$ $I_{rr} = 0.1 \cdot I_R, R_L = 100 \Omega$ | | | 3 | ns |

Note) 1. Rated input/output frequency: 100 MHz

2. * : t_{rr} measuring circuit



Marking Symbol: MU

Internal Connection

